

MITSUBISHI HIGH SPEED CMOS
M74HC253P/FP/DP

DUAL 4-INPUT DATA SELECTOR/MUX WITH 3-STATE OUTPUTS

DESCRIPTION

The M74HC253 is a semiconductor integrated circuit consisting of two 4-line to 1-line data selectors/multiplexers with 3-state outputs.

FEATURES

- High-speed: 18ns typ. ($C_L=15\text{pF}$, $V_{CC}=5\text{V}$)
- Low power dissipation: $20\mu\text{W}/\text{package, max}$ ($V_{CC}=5\text{V}$, $T_a=25^\circ\text{C}$, quiescent state)
- High noise margin: 30% of V_{CC} , min ($V_{CC}=4.5\text{V}, 6\text{V}$)
- Capable of driving 10 74LSTTL loads
- Wide supply voltage range: $V_{CC}=2\sim6\text{V}$
- Wide operating temperature range: $T_a=-40\sim+85^\circ\text{C}$

APPLICATION

General purpose, for use in industrial and consumer digital equipment.

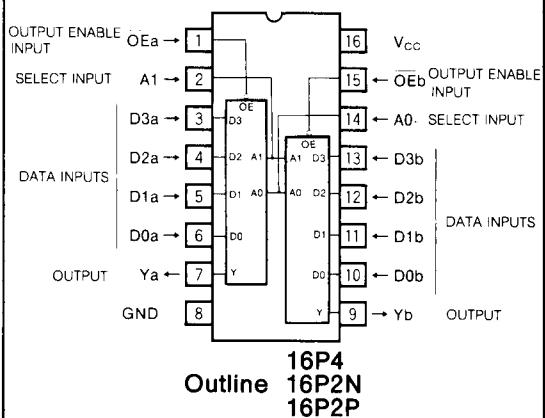
FUNCTIONAL DESCRIPTION

Use of silicon gate technology allows the M74HC253P to maintain the low power dissipation and high noise margin characteristics of the standard CMOS logic 4000B series while giving high-speed performance equivalent to the 74LS253.

The M74HC253 consists of data selector functions for selecting one of four input line signals and multiplex functions for converting 4-bit parallel data into serial data using time-division.

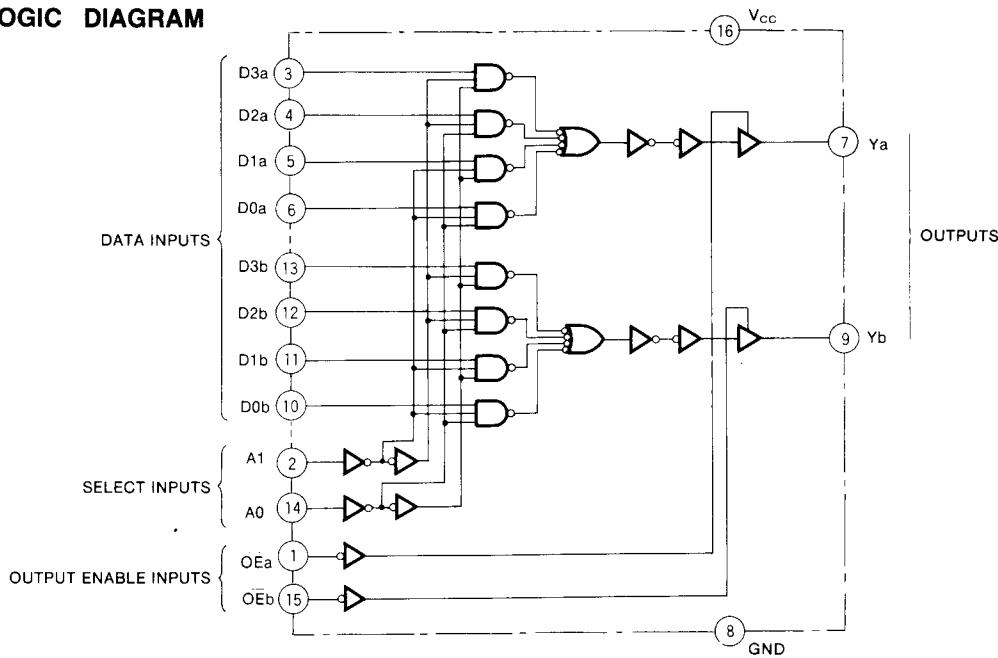
The 4-line signal is applied to data inputs D0 through D7, and after one of the data inputs has been selected by

PIN CONFIGURATION (TOP VIEW)



select inputs A0 and A1, that input signal will be output at Y. By applying 4-bit parallel data to D0 through D3, and connecting the output of a synchronous quadruple counter to A0 and A1, D0 through D3 data will be output at Y synchronous with the clock pulse in the order of D0-D3. Select inputs A are common to the two circuits while the output-enable inputs OE are independent. When OE is high, Y will become a high-impedance state irrespective of other inputs.

LOGIC DIAGRAM



DUAL 4-INPUT DATA SELECTOR/MUX WITH 3-STATE OUTPUTS

FUNCTION TABLE (Note 1)

Inputs							Output
A1	A0	D0	D1	D2	D3	OE	Y
X	X	X	X	X	X	H	Z
L	L	L	X	X	X	L	L
L	L	H	X	X	X	L	H
L	H	X	L	X	X	L	L
L	H	X	H	X	X	L	H
H	L	X	X	L	X	L	L
H	L	X	X	H	X	L	H
H	H	X	X	X	L	L	L
H	H	X	X	X	H	L	H

Note 1 : X : Irrelevant
Z : High impedance

ABSOLUTE MAXIMUM RATINGS ($T_a = -40\sim+85^\circ C$)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CC}	Supply voltage		-0.5~+7.0	V
V_I	Input voltage		-0.5~ $V_{CC}+0.5$	V
V_O	Output voltage		-0.5~ $V_{CC}+0.5$	V
I_{IK}	Input protection diode current	$V_I < 0V$	-20	mA
		$V_I > V_{CC}$	20	
I_{OK}	Output parasitic diode current	$V_O < 0V$	-20	mA
		$V_O > V_{CC}$	20	
I_O	Output current per output pin		± 25	mA
I_{CC}	Supply/GND current	V_{CC}, GND	± 50	mA
P_d	Power dissipation	(Note 2)	500	mW
T_{Stg}	Storage temperature range		-65~+150	°C

Note 2 : M74HC253FP, $T_a = -40\sim+70^\circ C$ and $T_a = 70\sim85^\circ C$ are derated at -6mW/°C.
M74HC253DP, $T_a = -40\sim+50^\circ C$ and $T_a = 50\sim85^\circ C$ are derated at -5mW/°C.

RECOMMENDED OPERATING CONDITIONS ($T_a = -40\sim+85^\circ C$)

Symbol	Parameter	Limits			Unit
		Min	Typ	Max	
V_{CC}	Supply voltage	2		6	V
V_I	Input voltage	0		V_{CC}	V
V_O	Output voltage	0		V_{CC}	V
T_{opr}	Operating temperature range	-40		+85	°C
t_r, t_f	Input risetime, falltime	$V_{CC} = 2.0V$	0	1000	ns
		$V_{CC} = 4.5V$	0	500	
		$V_{CC} = 6.0V$	0	400	

DUAL 4-INPUT DATA SELECTOR/MUX WITH 3-STATE OUTPUTS

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits						Unit	
			25°C			−40~+85°C				
			V _{CC} (V)	Min	Typ	Max	Min	Max		
V _{IH}	High-level input voltage	V _O = 0.1V, V _{CC} = 0.1V I _O = 20μA	2.0	1.5			1.5		V	
			4.5	3.15			3.15			
			6.0	4.2			4.2			
V _{IL}	Low-level input voltage	V _O = 0.1V, V _{CC} = 0.1V I _O = 20μA	2.0			0.5		0.5	V	
			4.5			1.35		1.35		
			6.0			1.8		1.8		
V _{OH}	High-level output voltage	V _I = V _{IH} , V _{IL}	I _{OH} = −20μA	2.0	1.9		1.9		V	
			I _{OH} = −20μA	4.5	4.4		4.4			
			I _{OH} = −20μA	6.0	5.9		5.9			
			I _{OH} = −4.0mA	4.5	4.18		4.13			
			I _{OH} = −5.2mA	6.0	5.68		5.63			
V _{OL}	Low-level output voltage	V _I = V _{IH} , V _{IL}	I _{OL} = 20μA	2.0			0.1		V	
			I _{OL} = 20μA	4.5			0.1			
			I _{OL} = 20μA	6.0			0.1			
			I _{OL} = 4.0mA	4.5			0.26			
			I _{OL} = 5.2mA	6.0			0.26			
I _{IH}	High-level input current	V _I = 6V		6.0			0.1		1.0 μA	
I _{IL}	Low-level input current	V _I = 0V		6.0			−0.1		−1.0 μA	
I _{OZH}	Off-state high-level output current	V _I = V _{IH} , V _{IL} , V _O = V _{CC}		6.0			0.5		5.0 μA	
I _{OZL}	Off-state low-level output current	V _I = V _{IH} , V _{IL} , V _O = GND		6.0			−0.5		−5.0 μA	
I _{CC}	Quiescent supply current	V _I = V _{CC} , GND, I _O = 0μA		6.0			4.0		40.0 μA	

SWITCHING CHARACTERISTICS (V_{CC} = 5V, T_A = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
t _{TLH}	Low-level to high-level and high-level to low-level output transition time				10	ns
t _{THL}					10	ns
t _{PLH}	Low-level to high-level and high-level to low-level output propagation time (D - Y)	C _L = 15pF (Note 4)			23	ns
t _{PHL}					23	ns
t _{PLH}	Low-level to high-level and high-level to low-level output propagation time (A - Y)				30	ns
t _{PHL}					30	ns
t _{PLZ}	Output disable time from low-level and high-level (OE - Y)				27	ns
t _{PHZ}		C _L = 5 pF (Note 4)			27	ns
t _{PZL}	Output enable time to low-level and high-level (OE - Y)				18	ns
t _{PZH}					18	ns

DUAL 4-INPUT DATA SELECTOR/MUX WITH 3-STATE OUTPUTS

SWITCHING CHARACTERISTICS ($V_{CC} = 2\sim 6V$, $T_a = -40\sim +85^\circ C$)

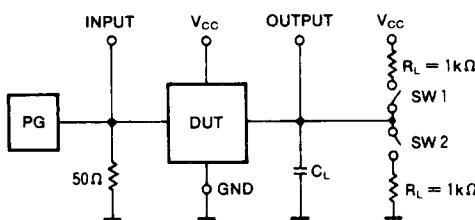
Symbol	Parameter	Test conditions	Limits					Unit	
			25°C		-40~+85°C				
			$V_{CC}(V)$	Min	Typ	Max	Min	Max	
t_{TLH}	Low-level to high-level and high-level to low-level output transition time	$C_L = 50pF$ (Note 4)	2.0			75		95	
			4.5			15		19	
			6.0			13		16	
	t_{PLH} Low-level to high-level and high-level to low-level output propagation time (D - Y)		2.0			75		95	
			4.5			15		19	
			6.0			13		16	
t_{PHL}	t_{PHL} Low-level to high-level and high-level to low-level output propagation time (A - Y)		2.0			126		158	
			4.5			28		35	
			6.0			23		29	
	t_{PHL} Low-level to high-level and high-level to low-level output propagation time (A - Y)		2.0			126		158	
			4.5			28		35	
			6.0			23		29	
t_{PLZ}	Output disable time from low-level and high-level ($\overline{OE} - Y$)		2.0			158		198	
			4.5			35		44	
			6.0			30		38	
	t_{PHZ} Output enable time to low-level and high-level ($\overline{OE} - Y$)		2.0			158		198	
			4.5			35		44	
			6.0			30		38	
t_{PZL}	Output enable time to low-level and high-level ($\overline{OE} - Y$)		2.0			135		169	
			4.5			30		38	
			6.0			25		31	
	t_{PZH} Output disable time from low-level and high-level ($\overline{OE} - Y$)		2.0			135		169	
			4.5			30		38	
			6.0			25		31	
C_I	Input capacitance	$OE = V_{CC}$				90		113	
	Off-state output capacitance					20		25	
	Power dissipation capacitance (Note 3)					17		21	
C_D						90		113	
C_O						20		25	
C_{PD}						17		21	
						10		10	
						15		15	
						61		pF	

Note 3 : C_{PD} is the internal capacitance of the IC calculated from operation supply current under no-load conditions.

The power dissipated during operation under no-load conditions is calculated using the following formula:

$$P_D = C_{PD} \cdot V_{CC}^2 \cdot f_t + I_{CC} \cdot V_{CC}$$

Note 4 : Test Circuit



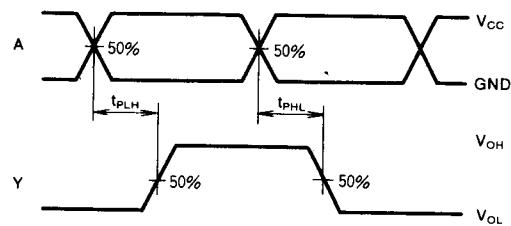
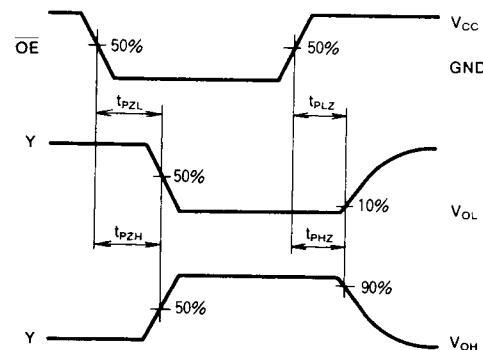
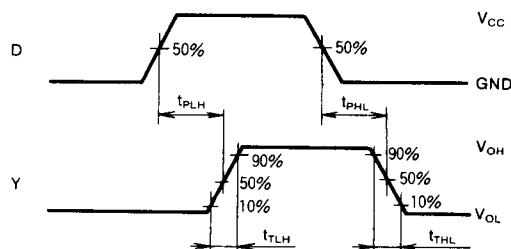
Parameter	SW 1	SW 2
t_{TLH}, t_{THL}	Open	Open
t_{PLH}, t_{PHL}	Closed	Open
t_{PLZ}	Open	Closed
t_{PZL}	Closed	Open
t_{PZH}	Open	Closed

(1) The pulse generator (PG) has the following characteristics (10%~90%): $t_r = 6ns$, $t_f = 6ns$

(2) The capacitance C_L includes stray wiring capacitance and the probe input capacitance.

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TIMING DIAGRAM



**MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES**

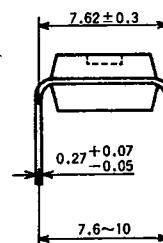
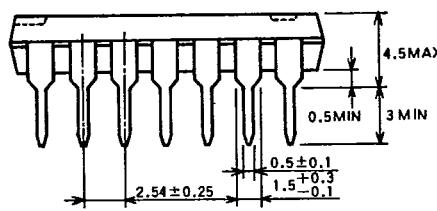
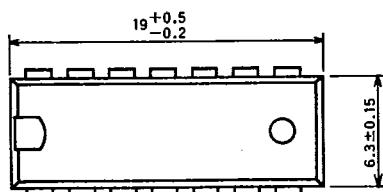
6249827 MITSUBISHI {DGTL LOGIC}

91D 12849

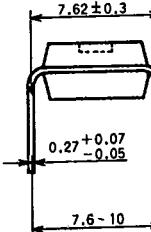
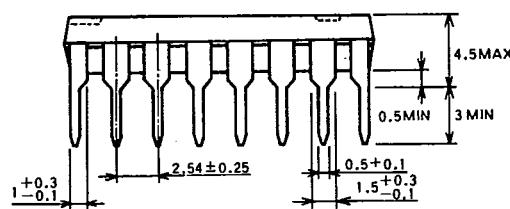
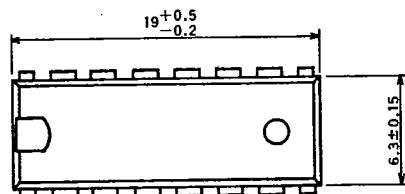
D T-90-20

TYPE 14P4 14-PIN MOLDED PLASTIC DIP

Dimension in mm

**TYPE 16P4 16-PIN MOLDED PLASTIC DIP**

Dimension in mm

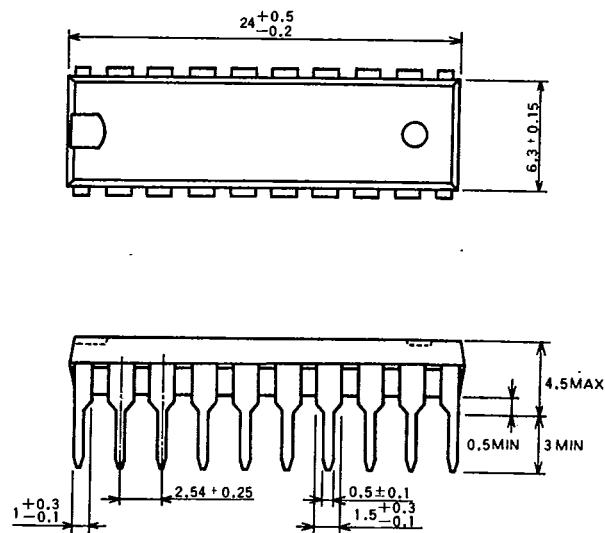


MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES

91D 12850 D T-90-20

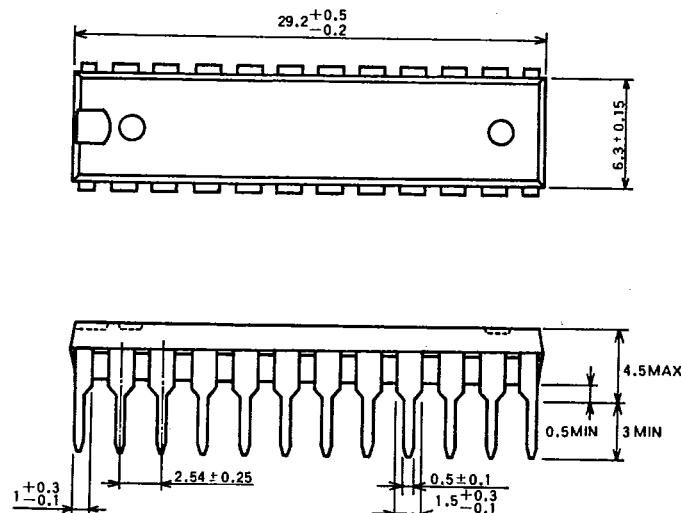
TYPE 20P4 20-PIN MOLDED PLASTIC DIP

Dimension in mm



TYPE 24P4D 24-PIN MOLDED PLASTIC DIP

Dimension in mm



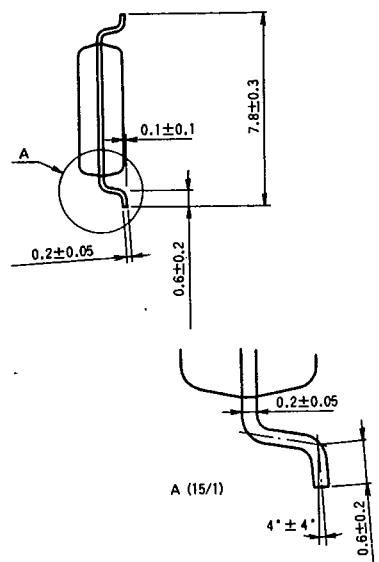
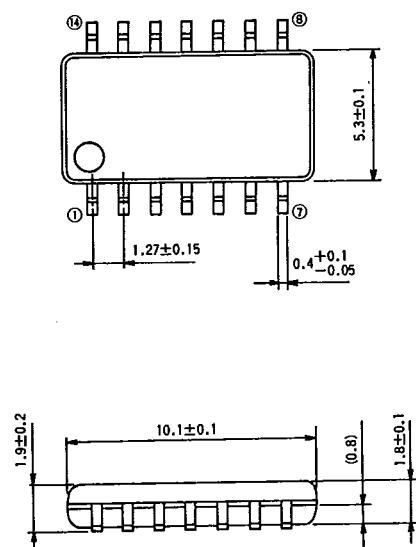
MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES

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91D 12851 D T-90.20

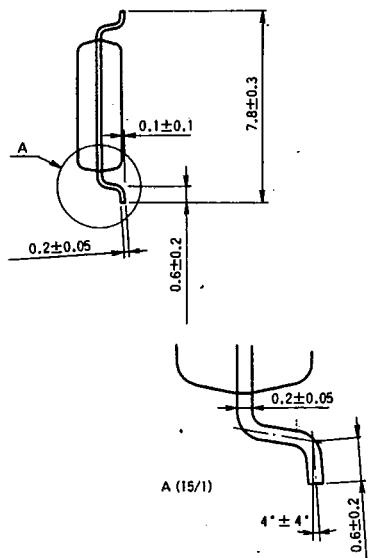
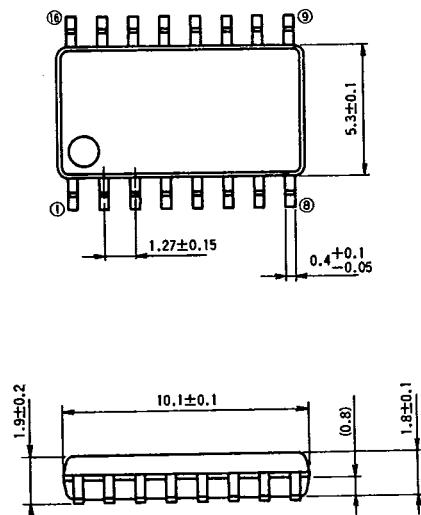
TYPE 14P2N 14PIN MOLDED PLASTIC SOP

Dimension in mm



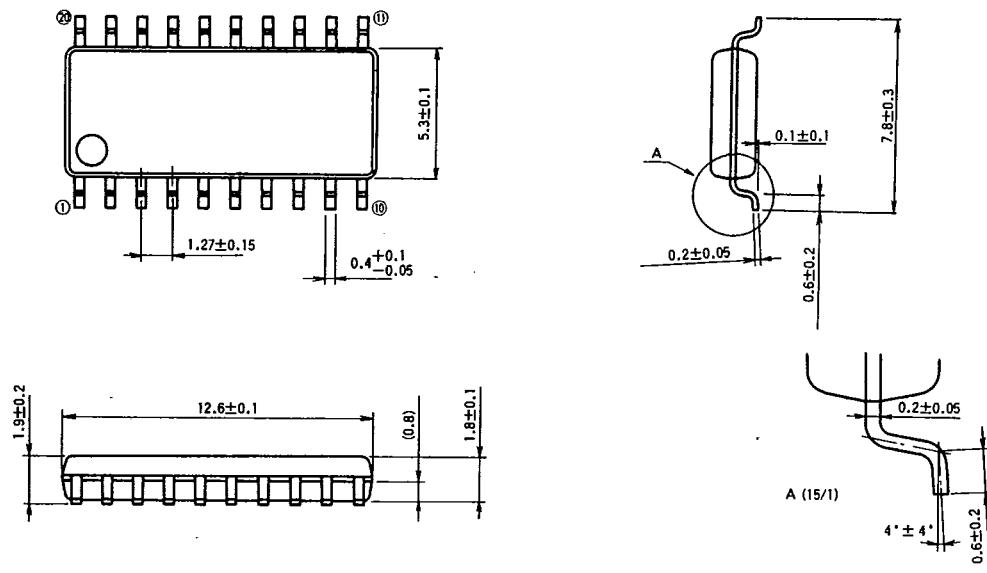
TYPE 16P2N 16PIN MOLDED PLASTIC SOP

Dimension in mm



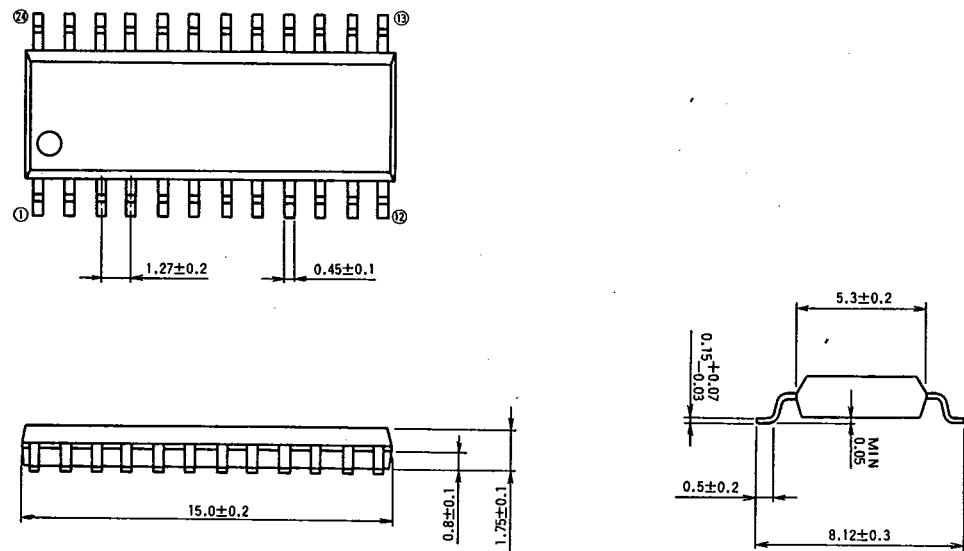
TYPE 20P2N 20PIN MOLDED PLASTIC SOP

Dimension in mm



TYPE 24P2 24PIN MOLDED PLASTIC SOP

Dimension in mm

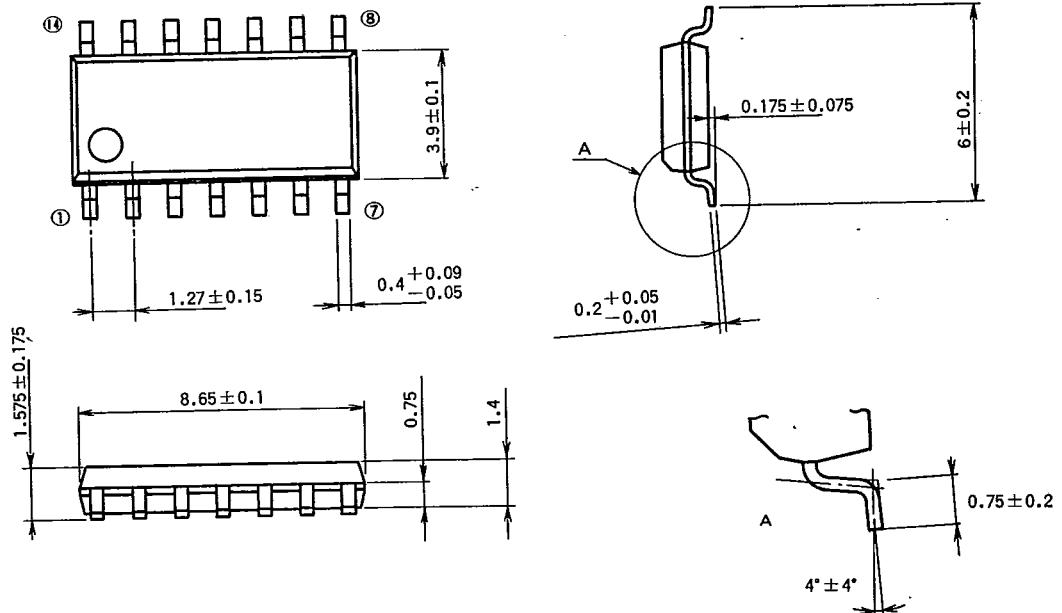


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91D 12853 D T90-20

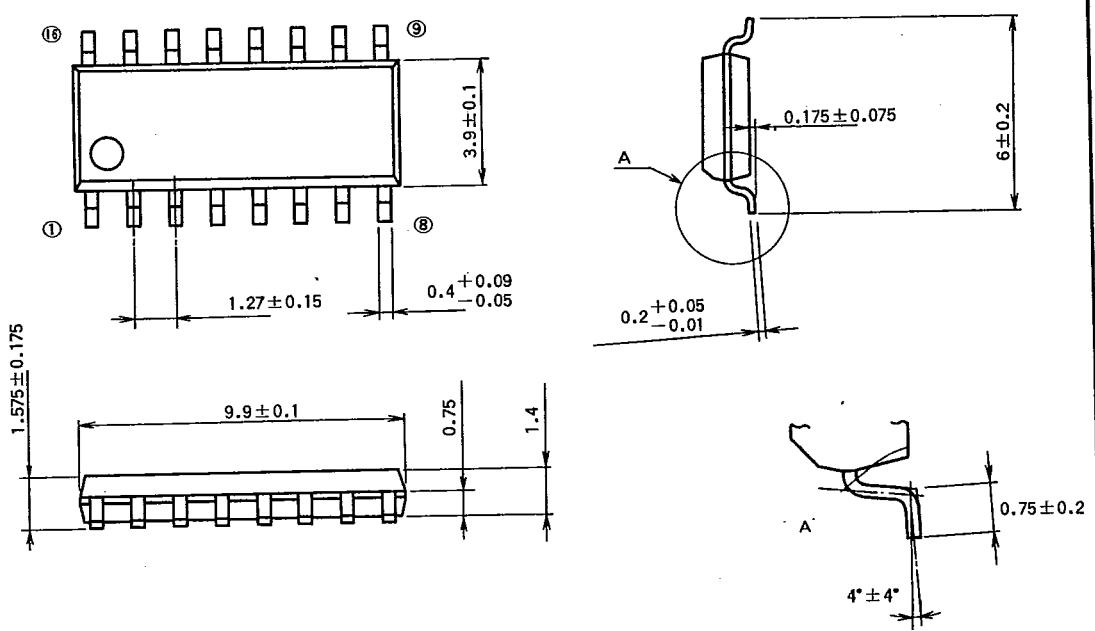
TYPE 14P2P 14-PIN MOLDED PLASTIC SOP(JEDEC 150mil body)

Dimension in mm



TYPE 16P2P 16-PIN MOLDED PLASTIC SOP(JEDEC 150mil body)

Dimension in mm



PACKAGE OUTLINES

6249827 MITSUBISHI (DGTL LOGIC)

91D 12854 D T-90-20

TYPE 20P2V 20-PIN MOLDED PLASTIC SOP(JEDEC 300mil body)

